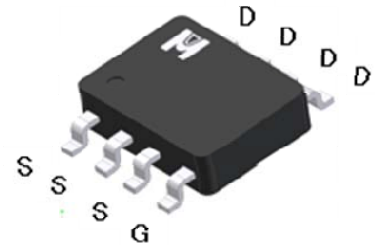
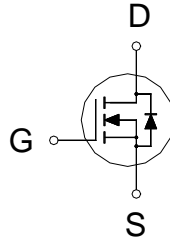




N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

$BV_{DSS}$	30V
$R_{DS(on)} (MAX.)$	6m $\Omega$
$I_D$	18A



UIS, Rg 100% Tested

Pb-Free Lead Plating

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ }^{\circ}\text{C}$  Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$	$I_D$	18	A
	$T_C = 100\text{ }^{\circ}\text{C}$		12	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	72	
Avalanche Current		$I_{AS}$	20	mJ
Avalanche Energy	$L = 0.1\text{mH}$ , $I_D = 20\text{A}$ , $R_G = 25\Omega$	$E_{AS}$	20	
Repetitive Avalanche Energy <sup>2</sup>	$L = 0.05\text{mH}$	$E_{AR}$	10	
Power Dissipation	$T_A = 25\text{ }^{\circ}\text{C}$	$P_D$	3	W
	$T_A = 100\text{ }^{\circ}\text{C}$		1.5	
Operating Junction & Storage Temperature Range		$T_{j}$ , $T_{stg}$	-55 to 175	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		25	$^{\circ}\text{C} / \text{W}$
Junction-to-Ambient <sup>3</sup>	$R_{\theta JA}$		50	

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Duty cycle  $\leq 1\%$

<sup>3</sup>50 $^{\circ}\text{C} / \text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



ELECTRICAL CHARACTERISTICS ( $T_A = 25\text{ }^{\circ}\text{C}$ , Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24V, V_{GS} = 0V$			1	$\mu A$
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			25	
On-State Drain Current <sup>1</sup>	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	12			A
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 18A$		5.3	6	m $\Omega$
		$V_{GS} = 4.5V, I_D = 12A$		7.5	9.5	
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 5V, I_D = 18A$		25		S
DYNAMIC						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		1983		pF
Output Capacitance	$C_{oss}$			328		
Reverse Transfer Capacitance	$C_{rss}$			287		
Gate Resistance	$R_g$	$V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$		1.2		$\Omega$
Total Gate Charge <sup>1,2</sup>	$Q_g(V_{GS}=10V)$	$V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 18A$		41		nC
	$Q_g(V_{GS}=4.5V)$			23		
Gate-Source Charge <sup>1,2</sup>	$Q_{gs}$			6		
Gate-Drain Charge <sup>1,2</sup>	$Q_{gd}$			13		
Turn-On Delay Time <sup>1,2</sup>	$t_{d(on)}$	$V_{DS} = 15V,$ $I_D = 1A, V_{GS} = 10V, R_{GS} = 2.7\Omega$		9		nS
Rise Time <sup>1,2</sup>	$t_r$			20		
Turn-Off Delay Time <sup>1,2</sup>	$t_{d(off)}$			25		
Fall Time <sup>1,2</sup>	$t_f$			3		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T <sub>c</sub> = 25 °C)						
Continuous Current	$I_S$				4	A
Pulsed Current <sup>3</sup>	$I_{SM}$				40	
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = I_S, V_{GS} = 0V$			1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F = I_S, dI_F/dt = 100A / \mu S$		32		nS
Peak Reverse Recovery Current	$I_{RM(REC)}$			40		A
Reverse Recovery Charge	$Q_{rr}$			12		nC

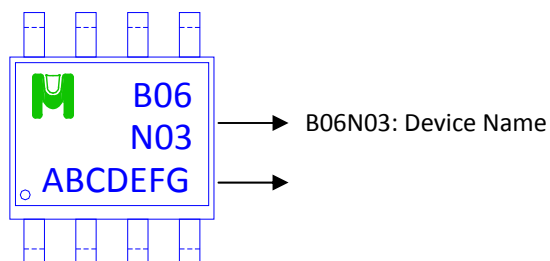
<sup>1</sup>Pulse test : Pulse Width  $\leq 300 \mu\text{sec}$ , Duty Cycle  $\leq 2\%$ .

<sup>2</sup>Independent of operating temperature.

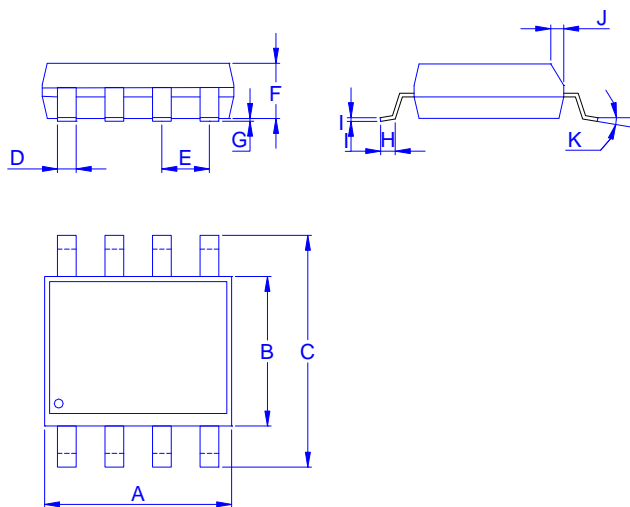
<sup>3</sup>Pulse width limited by maximum junction temperature.

### Ordering & Marking Information:

Device Name: EMB06N03G for SOP-8



### Outline Drawing



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K
in.	4.70	3.70	5.80	0.33		1.20	0.08	0.40	0.19	0.25	0°
Typ.					1.27						
Max.	5.10	4.10	6.20	0.51		1.62	0.28	0.83	0.26	0.50	8°

